2018년 2월 7일(수), 10:45-12:15 Room F (봉래I, 6층)

F. Silicon and Group-IV Devices and Integration Technology 분과 [WF2-F] Reliability

WF2-F-1 10:45-11:00	Investigation of PBTI Characteristics of FD-SOI TFET with High-k Dielectric Hyeong-Sub Song ¹ , So-Yeong Kim ¹ , Sung-Kyu Kwon ¹ , Dong-Hwan Lim ² , Chang- Hwan Choi ² , Ga-Won Lee ¹ , and Hi-Deok Lee ¹ ¹ Department of Electronics Engineering, Chungnam National University, ² Division of Materials Science and Engineering, Hanyang University
WF2-F-2 11:00-11:15	Investigation on Negative Differential Transconductance (NDT) of Double- Gate Tunnel FETs Jang Woo Lee and Woo Young Choi Department of Electronic Engineering, Sogang University
WF2-F-3 11:15-11:30	Gate Voltage Dependence of Low Frequency Noise in Tunneling Field Effect Transistor So-Yeong Kim ¹ , Hyeong-Sub Song ¹ , Sung-Kyu Kwon ¹ , Dong-Hwan Lim ² , Chang- Hwan Choi ² , Ga-Won Lee ¹ , and Hi-Deok Lee ¹ ¹ Department of Electronics Engineering, Chungnam National University, ² Division of Materials Science and Engineering, Hanyang University
WF2-F-4 11:30-11:45	Ge 기반의 소자에서 Y-ZrO2 게이트 유전체를 이용한 EOT 스케일링 (~5.7Å) 및 누설 전류와 계면 트랩의 감소 Tae In Lee, Min Ju Kim, Manh-Cuong Nguyen, Hyun Jun Ahn, Jungmin Moon, Tae Yoon Lee, Hyun-Young Yu, Rino Choi, Wan Sik Hwang, and Byung Jin Cho School of Electrical Engineering, KAIST
WF2-F-5 11:45-12:00	Simple and Scalable N-Type Conversion of Semiconducting Carbon Nanotube Thin Film Transistors Using X-Layer/SU8 Passivation Seung Yeop Kim, Geon Woong Lim, Eun Bin Roh, Geun Woo Baek, and Sung Hun Jin Department of Electronic Engineering, Incheon National University
WF2-F-6 12:00-12:15	Fabrication of High Quality Gate Insulator in Metal-Oxide-Semiconductor Capacitor Using Laser Annealing Kyoung Moon Yu, Hyung Min Ji, Manh-Cuong Nguyen, An Hoang-Thuy Nguyen, Jung Yeon Kim, Sujin Choi, Jonggyu Cheon, Jin Hyun Kim, Sang Woo Kim, Seong Yong Cho, and Rino Choi Department of Materials Science and Engineering, Inha University